Abstracts

11 GHz Bandwidth GaAs MESFET/MSM OEIC Receivers

J.S. Wang, C.G. Shih, W.H. Chang, J. Middleton, P.J. Apostolakis and M. Feng. "11 GHz Bandwidth GaAs MESFET/MSM OEIC Receivers." 1993 MTT-S International Microwave Symposium Digest 93.2 (1993 Vol. II [MWSYM]): 1047-1050.

We report state-of-the-art performance of direct ion implanted GaAs-MESFET with a 0.6 µm gate length and MSM based OEIC receiver achieving a -3 dB bandwidth as high as 11 GHz for optical signals at the wavelength of 850 nm. The feedback resistance of the receiver is 1000 Omega and the effective transimpedance is 565 Omega into a 50 Omega load. The effective transimpedance-bandwidth (TZBW) product is 6.1 THz-Omega for this receiver.

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